/ Descriptions

WR0585 ṂṂ Ł SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

ㅊ` Ⅵ ɔ я ı ‖ Ḅ[OBJ]ὼ ᵶ ɻ ό ı ゔ ᑐ ڀ ŕ PEŁW ʹH

High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity

[redacted]

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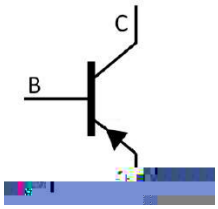
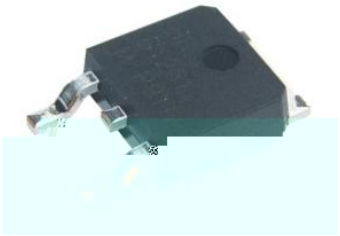
High voltage driver applications.



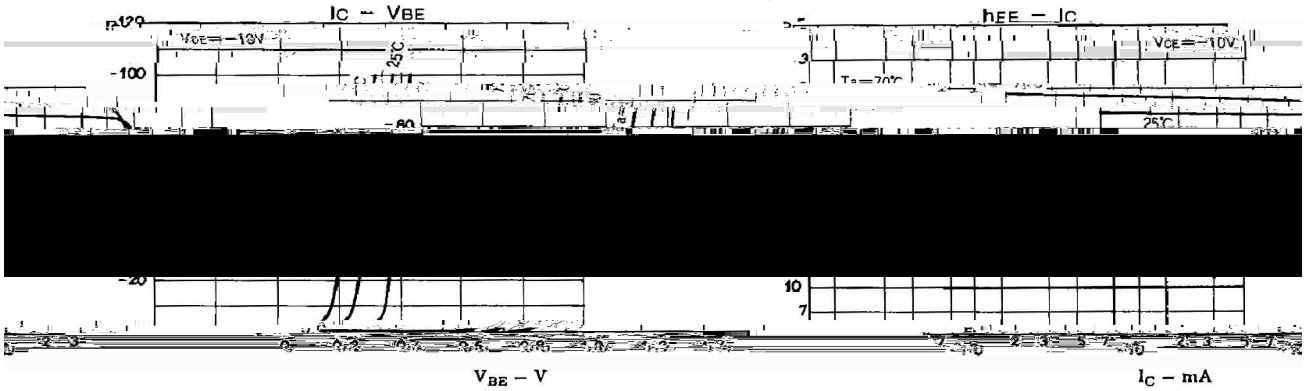


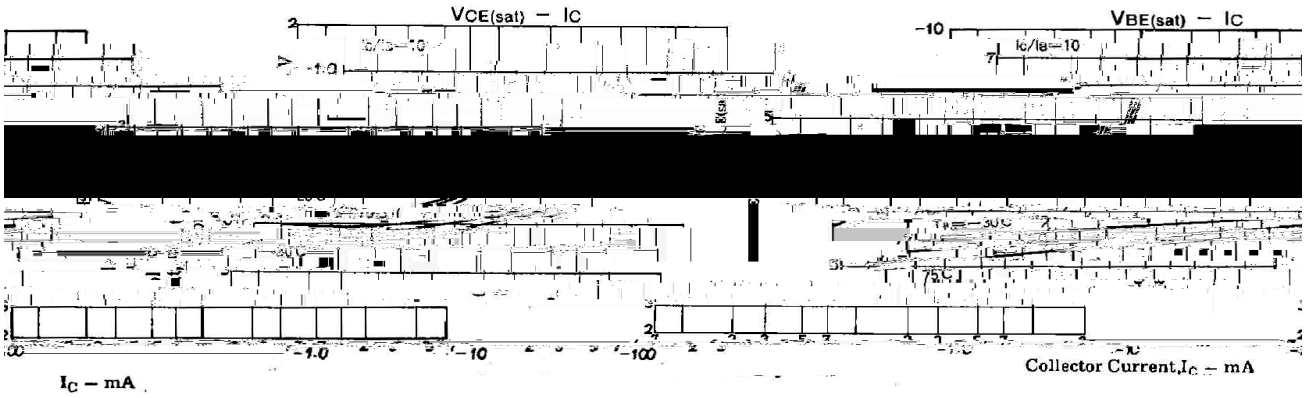
PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

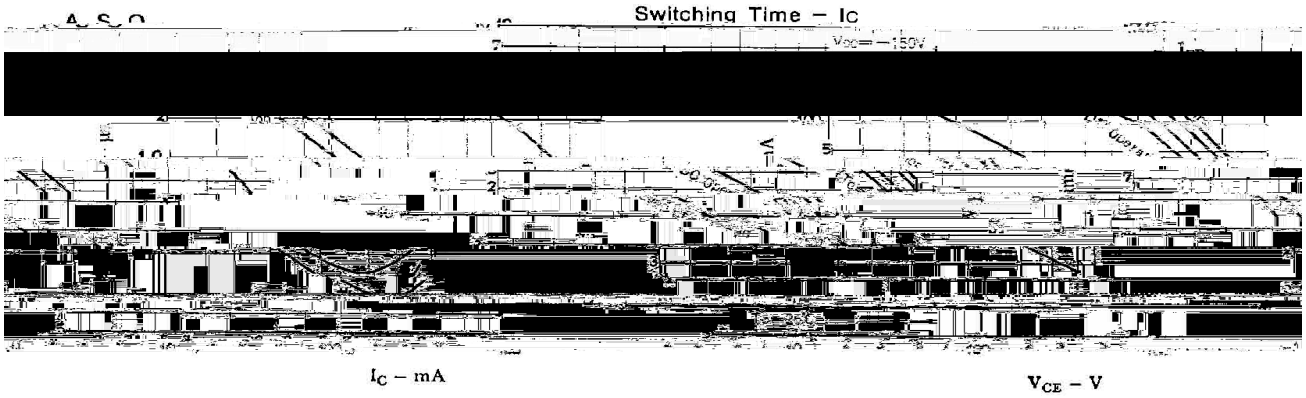
/ h_{FE} Classifications & Marking

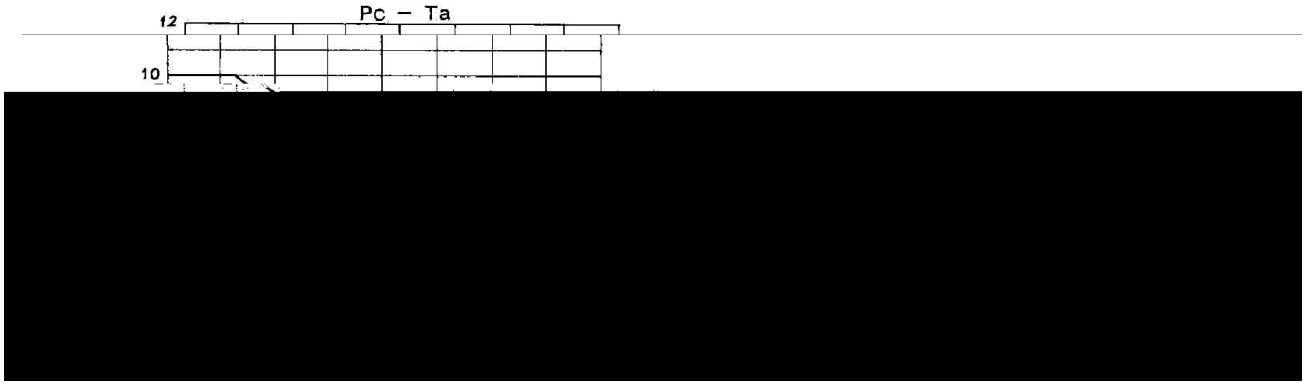
v ˝Ω Parameter	ϒ N Symbol	˝Ω Ө Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	-400	V

/ Electrical Characteristic Curve

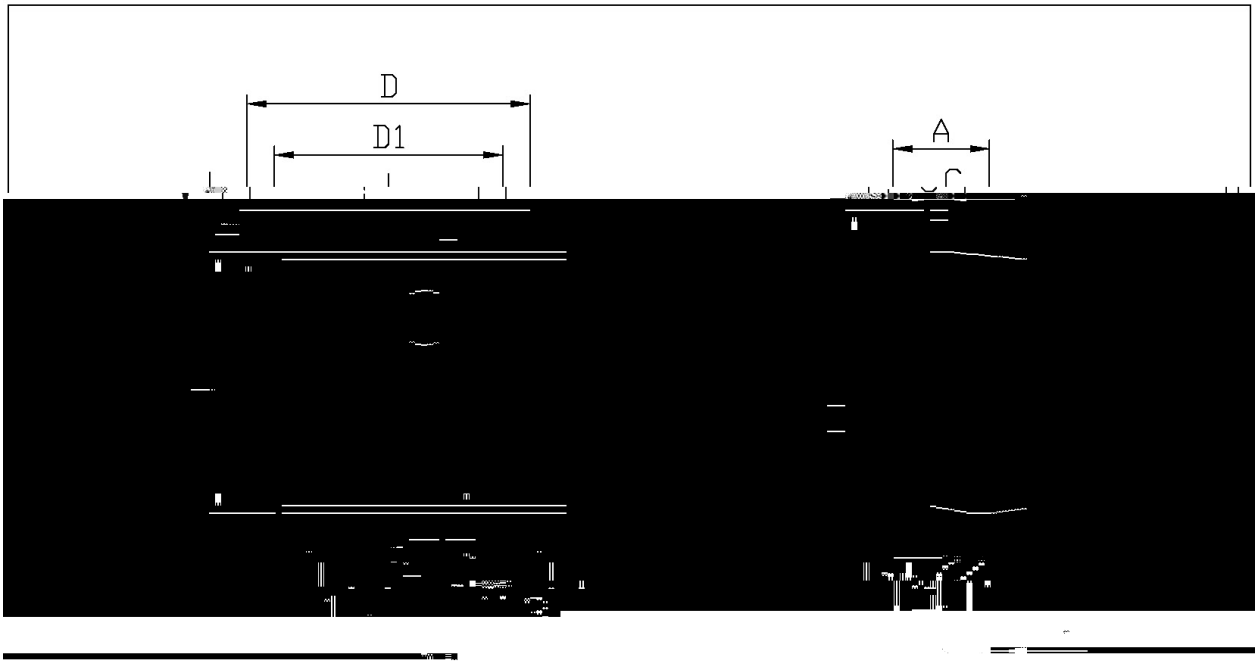






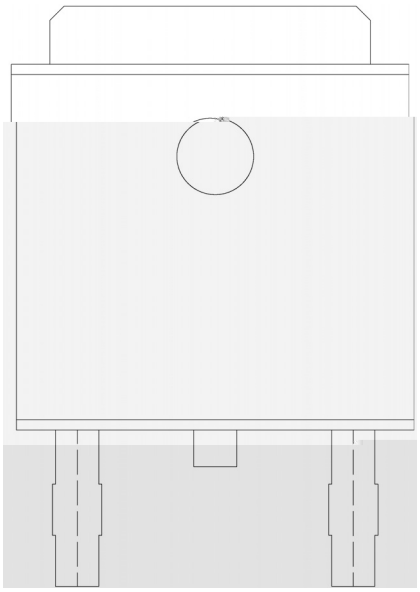


/ Package Dimensions



	4.75				
	0.95	b1	0.45	0.55	L1	0.45
25	1.75	C	0.45	0.55	L2	1.
.60	0.90	D	6.45	6.75	L3	0
0.00	0.10	D1	5.10	5.50	K	

/ Marking Instructions



ِ ˝ χ

BR χ ѭ ϛ И Ґ

A1700 χ ѭ ϛ N Ґ

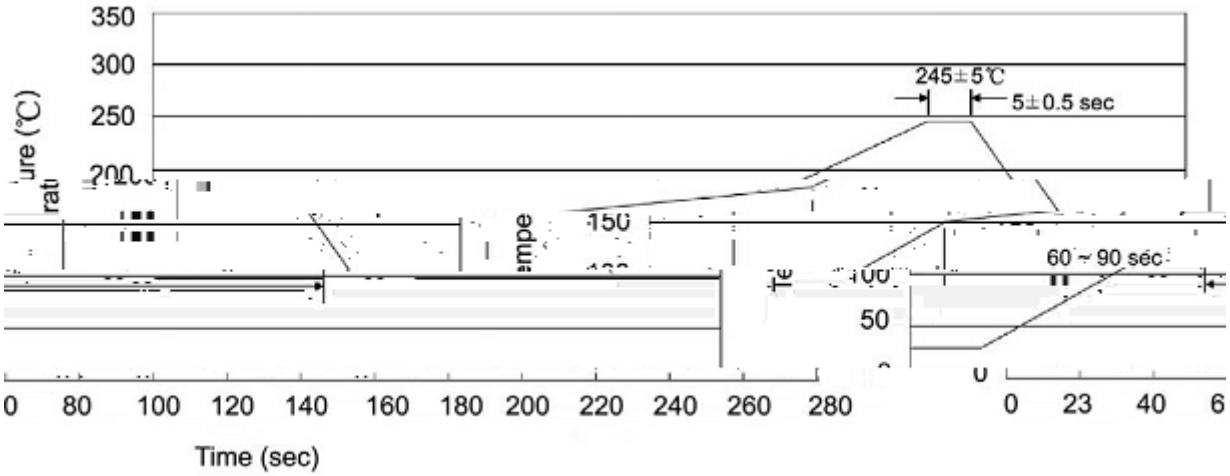
D= ѭ h_{FE} ‘ 6 Ґ

---- χ ѭ ı ғ ń N Ґ ı ɕ ı ғ ń N Ψ ק

Note:

BR: A13( )Tj22[ ]TJ7 W n DFÖ

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ɬ ı ˋH ڑ ˋY ʌ ㎛ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ♭ ỷ ㎛ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ɬ	ˋH ڑ χ 10 ° 1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

ɔ ` ϒ Ł / REEL

Package Type	Units	Dimension	(unit mm^3)